



Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding Embedded - FPGAs (Field Programmable Gate Array)

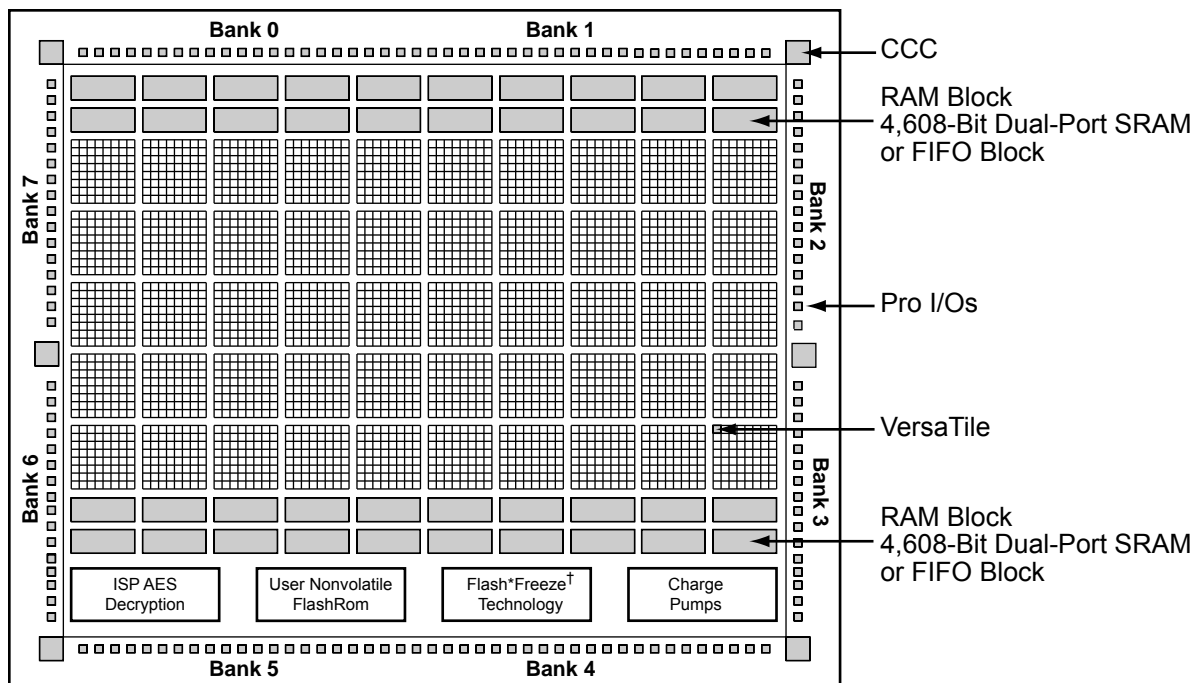
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	71
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn060-1vqg100



Note: Flash*Freeze technology only applies to IGL00e devices.

Figure 1-7 • IGL00e and ProASIC3E Device Architecture Overview (AGLE600 device is shown)

I/O State of Newly Shipped Devices

Devices are shipped from the factory with a test design in the device. The power-on switch for VCC is OFF by default in this test design, so I/Os are tristated by default. Tristated means the I/O is not actively driven and floats. The exact value cannot be guaranteed when it is floating. Even in simulation software, a tristate value is marked as unknown. Due to process variations and shifts, tristated I/Os may float toward High or Low, depending on the particular device and leakage level.

If there is concern regarding the exact state of unused I/Os, weak pull-up/pull-down should be added to the floating I/Os so their state is controlled and stabilized.

Simple Design Example

Consider a design consisting of six building blocks (shift registers) and targeted for an A3PE600-PQ208 (Figure 3-16 on page 52). The example design consists of two PLLs (PLL1 has GLA only; PLL2 has both GLA and GLB), a global reset (ACLR), an enable (EN_ALL), and three external clock domains (QCLK1, QCLK2, and QCLK3) driving the different blocks of the design. Note that the PQ208 package only has two PLLs (which access the chip global network). Because of fanout, the global reset and enable signals need to be assigned to the chip global resources. There is only one free chip global for the remaining global (QCLK1, QCLK2, QCLK3). Place two of these signals on the quadrant global resource. The design example demonstrates manually assignment of QCLK1 and QCLK2 to the quadrant global using the PDC command.

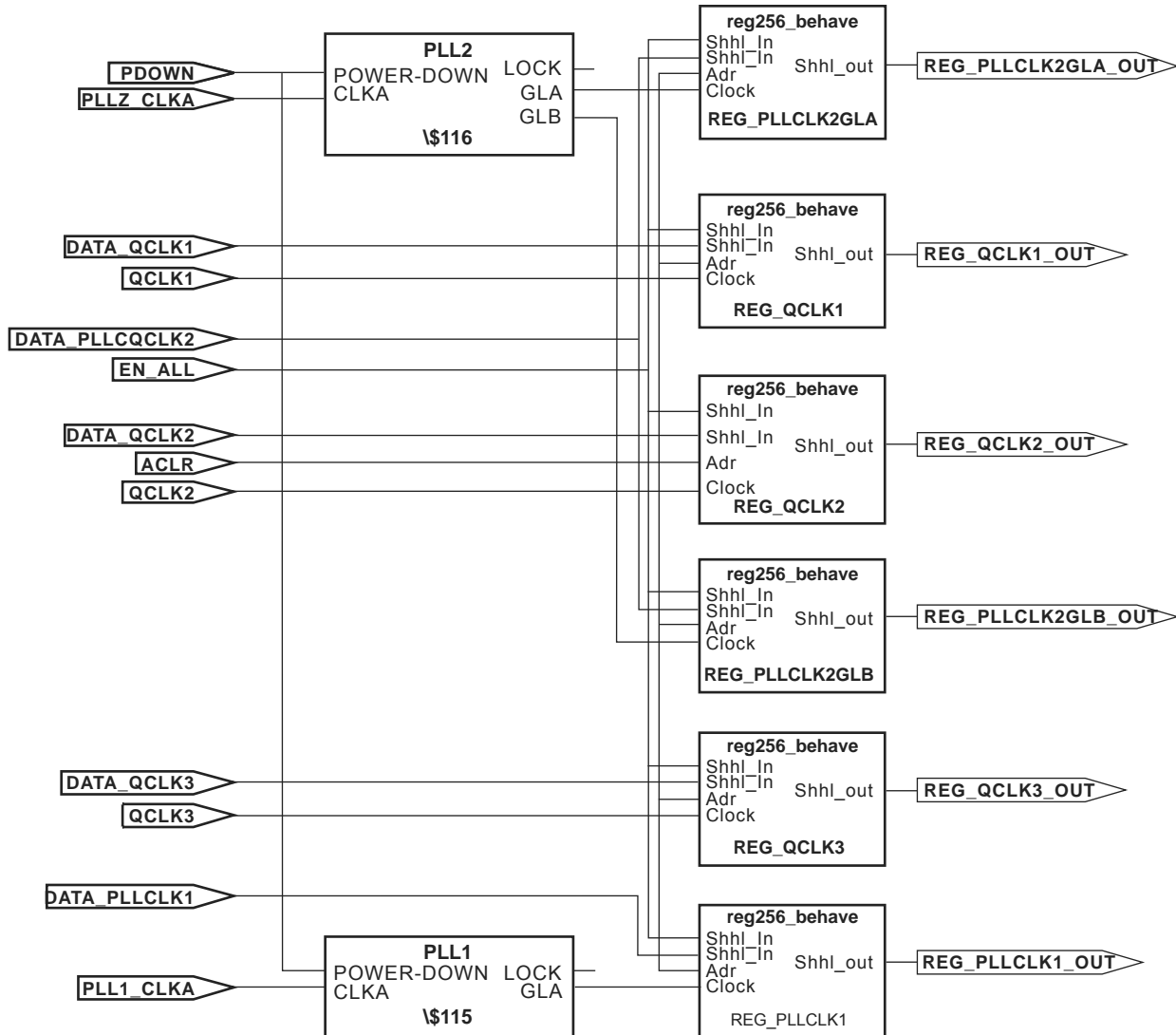


Figure 3-19 • Block Diagram of the Global Management Example Design

Step 1

Run Synthesis with default options. The Synplicity log shows the following device utilization:

Cell usage:

	cell count	area	count*area
DFN1E1C1	1536	2.0	3072.0
BUFF	278	1.0	278.0
INBUF	10	0.0	0.0
VCC	9	0.0	0.0
GND	9	0.0	0.0
OUTBUF	6	0.0	0.0
CLKBUF	3	0.0	0.0
PLL	2	0.0	0.0
TOTAL	1853		3350.0

Step 2

Run Compile with the **Promote regular nets whose fanout is greater than** option selected in Designer; you will see the following in the Compile report:

Device utilization report:

```
=====
CORE                Used:   1536 Total:  13824 (11.11%)
IO (W/ clocks)      Used:    19 Total:   147 (12.93%)
Differential IO      Used:     0 Total:    65 (0.00%)
GLOBAL              Used:     8 Total:    18 (44.44%)
PLL                 Used:     2 Total:     2 (100.00%)
RAM/FIFO            Used:     0 Total:    24 (0.00%)
FlashROM            Used:     0 Total:     1 (0.00%)
=====
```

The following nets have been assigned to a global resource:

Fanout	Type	Name

1536	INT_NET	Net : EN_ALL_c Driver: EN_ALL_pad_CLKINT Source: AUTO PROMOTED
1536	SET/RESET_NET	Net : ACLR_c Driver: ACLR_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : QCLK1_c Driver: QCLK1_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : QCLK2_c Driver: QCLK2_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : QCLK3_c Driver: QCLK3_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : \$1N14 Driver: \$1I5/Core Source: ESSENTIAL
256	CLK_NET	Net : \$1N12 Driver: \$1I6/Core Source: ESSENTIAL
256	CLK_NET	Net : \$1N10 Driver: \$1I6/Core Source: ESSENTIAL

Designer will promote five more signals to global due to high fanout. There are eight signals assigned to global networks.

Initializing the RAM/FIFO

The SRAM blocks can be initialized with data to use as a lookup table (LUT). Data initialization can be accomplished either by loading the data through the design logic or through the UJTAG interface. The UJTAG macro is used to allow access from the JTAG port to the internal logic in the device. By sending the appropriate initialization string to the JTAG Test Access Port (TAP) Controller, the designer can put the JTAG circuitry into a mode that allows the user to shift data into the array logic through the JTAG port using the UJTAG macro. For a more detailed explanation of the UJTAG macro, refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 117.

A user interface is required to receive the user command, initialization data, and clock from the UJTAG macro. The interface must synchronize and load the data into the correct RAM block of the design. The main outputs of the user interface block are the following:

- Memory block chip select: Selects a memory block for initialization. The chip selects signals for each memory block that can be generated from different user-defined pockets or simple logic, such as a ring counter (see below).
- Memory block write address: Identifies the address of the memory cell that needs to be initialized.
- Memory block write data: The interface block receives the data serially from the UTDI port of the UJTAG macro and loads it in parallel into the write data ports of the memory blocks.
- Memory block write clock: Drives the WCLK of the memory block and synchronizes the write data, write address, and chip select signals.

Figure 6-8 shows the user interface between UJTAG and the memory blocks.

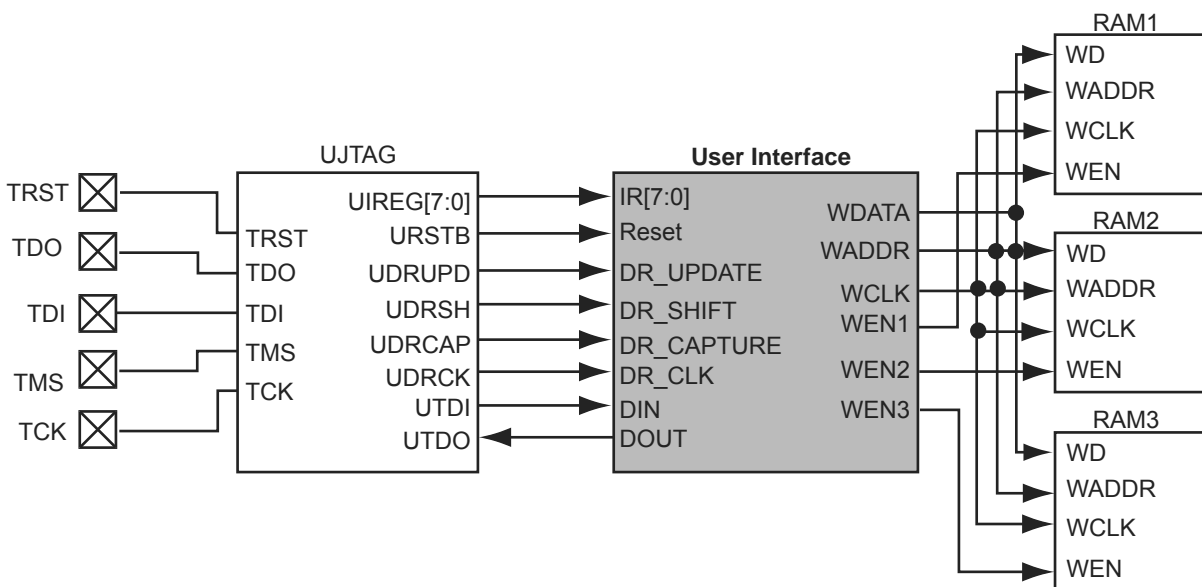


Figure 6-8 • Interfacing TAP Ports and SRAM Blocks

An important component of the interface between the UJTAG macro and the RAM blocks is a serial-in/parallel-out shift register. The width of the shift register should equal the data width of the RAM blocks. The RAM data arrives serially from the UTDI output of the UJTAG macro. The data must be shifted into a shift register clocked by the JTAG clock (provided at the UDRCK output of the UJTAG macro).

Then, after the shift register is fully loaded, the data must be transferred to the write data port of the RAM block. To synchronize the loading of the write data with the write address and write clock, the output of the shift register can be pipelined before driving the RAM block.

The write address can be generated in different ways. It can be imported through the TAP using a different instruction opcode and another shift register, or generated internally using a simple counter. Using a counter to generate the address bits and sweep through the address range of the RAM blocks is

I/O Architecture

I/O Tile

IGLOO and ProASIC3 nano devices utilize either a single-tile or dual-tile I/O architecture (Figure 7-1 on page 159 and Figure 7-2 on page 160). The 10 k, 15 k, and 20 k devices utilize the single-tile design and the 60 k, 125 k and 250 k devices utilize the dual-tile design. In both cases, the I/O tile provides a flexible, programmable structure for implementing a large number of I/O standards. In addition, the registers available in the I/O tile can be used to support high-performance register inputs and outputs, with register enable if desired. For single-tile designs, all I/O registers share both the CLR and CLK ports, while for the dual-tile designs, the output register and output enable register share one CLK port. For the dual-tile designs, the registers can also be used to support the JESD-79C Double Data Rate (DDR) standard within the I/O structure (see the "DDR for Microsemi's Low Power Flash Devices" section on page 205 for more information).

I/O Registers

Each I/O module contains several input and output registers. Refer to Figure 7-3 on page 165 for a simplified representation of the I/O block. The number of input registers is selected by a set of switches (not shown in Figure 7-2 on page 160) between registers to implement single-ended data transmission to and from the FPGA core. The Designer software sets these switches for the user. For single-tile designs, a common CLR/PRE signal is employed by all I/O registers when I/O register combining is used. The I/O register combining requires that no combinatorial logic be present between the register and the I/O.

- If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
 - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
 - If the clear or preset pins are present, they must have the same polarity.
 - If the clear or preset pins are present, they must be driven by the same signal (net).
3. For single-tile devices (10 k, 15 k, and 20 k): Registers connected to an I/O on the Output and Output Enable pins must have the same clock function (both CLR and CLK are shared among all registers):
 - Both the Output and Output Enable registers must not have an E pin (clock enable).
 4. For dual-tile devices (60 k, 125 k, and 250 k): Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
 - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
 - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a buffer while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes -----register will combine
set_preserve <signal name> ----register will not combine
```

Weak Pull-Up and Weak Pull-Down Resistors

nano devices support optional weak pull-up and pull-down resistors on each I/O pin. When the I/O is pulled up, it is connected to the V_{CCI} of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications and when using IGLOO nano devices, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash*Freeze mode. Refer to "Flash*Freeze Technology and Low Power Modes" in an applicable FPGA fabric user's guide for more information.

The Flash*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic LOW to logic HIGH or vice versa.

It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions.

The slew rate can be implemented by using a PDC command (Table 7-5 on page 163), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."

Microsemi recommends the high slew rate option to minimize the propagation delay. This high-speed option may introduce noise into the system if appropriate signal integrity measures are not adopted. Selecting a low slew rate reduces this kind of noise but adds some delays in the system. Low slew rate is recommended when bus transients are expected.

Output Drive

The output buffers of nano devices can provide multiple drive strengths to meet signal integrity requirements. The LVTTTL and LVCMOS (except 1.2 V LVCMOS) standards have selectable drive strengths.

Drive strength should also be selected according to the design requirements and noise immunity of the system.

User I/O Naming Convention

Due to the comprehensive and flexible nature of nano Standard I/Os, a naming scheme is used to show the details of each I/O (Figure 7-8). The name identifies to which I/O bank it belongs.

I/O Nomenclature = FF/Gmn/IOuxwBy

Gmn is only used for I/Os that also have CCC access—i.e., global pins.

FF = Indicates the I/O dedicated for the Flash*Freeze mode activation pin

G = Global

m = Global pin location associated with each CCC on the device: A (northwest corner), B (northeast corner), C (east middle), D (southeast corner), E (southwest corner), and F (west middle)

n = Global input MUX and pin number of the associated Global location m—either A0, A1, A2, B0, B1, B2, C0, C1, or C2. Refer to the "Global Resources in Low Power Flash Devices" section on page 31 for information about the three input pins per clock source MUX at CCC location m.

u = I/O pair number in the bank, starting at 00 from the northwest I/O bank and proceeding in a clockwise direction

x = R (Regular—single-ended) for the I/Os that support single-ended standards.

w = S (Single-Ended)

B = Bank

y = Bank number (0–3). The Bank number starts at 0 from the northwest I/O bank and proceeds in a clockwise direction.

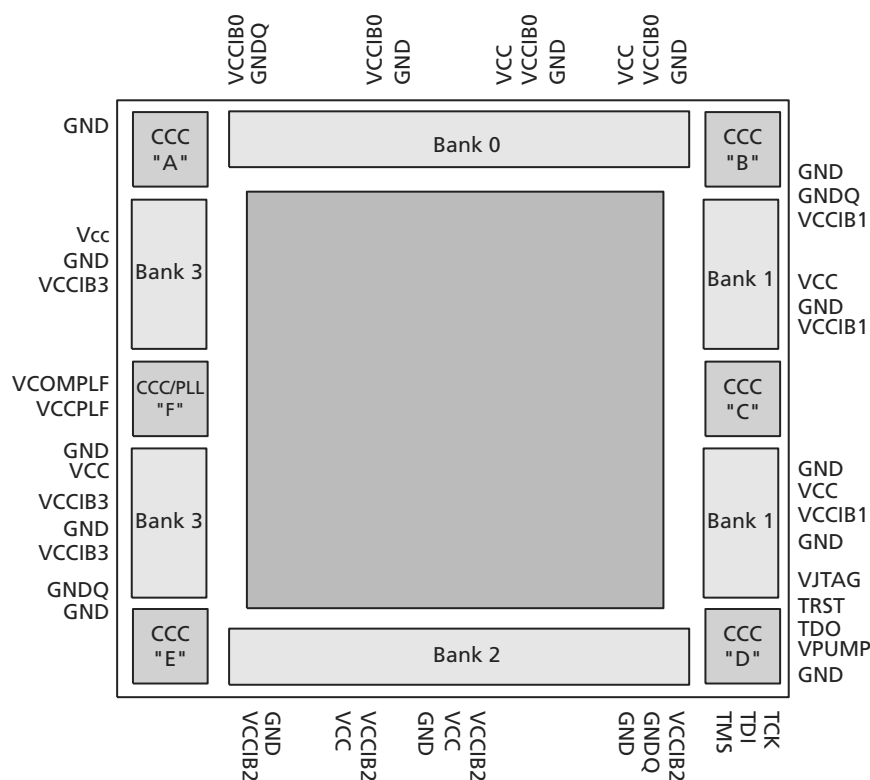


Figure 7-8 • I/O Naming Conventions for nano Devices – Top View

Related Documents

Application Notes

Board-Level Considerations

http://www.microsemi.com/soc/documents/ALL_AC276_AN.pdf

User's Guides

Libero SoC User's Guide

http://www.microsemi.com/soc/documents/libero_ug.pdf

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide

http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf

SmartGen Core Reference Guide

http://www.microsemi.com/soc/documents/genguide_ug.pdf

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Changes	Page
August 2012	Figure 7-2 • I/O Block Logical Representation for Dual-Tile Designs (60 k, 125 k, and 250 k Devices) was revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low (SAR 40698).	160
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663).	181, 183
June 2011	Figure 7-2 • I/O Block Logical Representation for Dual-Tile Designs (60 k, 125 k, and 250 k Devices) was revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).	160
	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V–tolerant CMOS input buffer and a push-pull output buffer."	166
	The "5 V Input Tolerance" section was revised to state that 5 V input tolerance can be used with LVTTTL 3.3 V and LVCMOS 3.3 V configurations. LVCMOS 2.5 V, LVCMOS 1.8 V, LVCMOS 1.5 V, and LVCMOS 1.2 V were removed from the sentence listing supported configurations (SAR 22427).	171

Compiling the Design

During Compile, a PDC I/O constraint file can be imported along with the netlist file. If only the netlist file is compiled, certain I/O assignments need to be completed before proceeding to Layout. All constraints that can be entered in PDC can also be entered using ChipPlanner, I/O Attribute Editor, and PinEditor.

There are certain rules that must be followed in implementing I/O register combining and the I/O DDR macro (refer to the I/O Registers section of the handbook for the device that you are using and the "DDR" section on page 190 for details). Provided these rules are met, the user can enable or disable I/O register combining by using the PDC command `set_io portname -register yes|no` in the I/O Attribute Editor or selecting a check box in the Compile Options dialog box (see Figure 8-7). The Compile Options dialog box appears when the design is compiled for the first time. It can also be accessed by choosing **Options > Compile** during successive runs. I/O register combining is off by default. The PDC command overrides the setting in the Compile Options dialog box.

Figure 8-7 • Setting Register Combining During Compile

Understanding the Compile Report

The I/O bank report is generated during Compile and displayed in the log window. This report lists the I/O assignments necessary before Layout can proceed.

When Designer is started, the I/O Bank Assigner tool is run automatically if the Layout command is executed. The I/O Bank Assigner takes care of the necessary I/O assignments. However, these assignments can also be made manually with MVN or by importing the PDC file. Refer to the "Assigning Technologies and VREF to I/O Banks" section on page 198 for further description.

The I/O bank report can also be extracted from Designer by choosing **Tools > Report** and setting the Report Type to **IOBank**.

This report has the following tables: I/O Function, I/O Technology, I/O Bank Resource Usage, and I/O Voltage Usage. This report is useful if the user wants to do I/O assignments manually.

I/O Function

Figure 8-8 shows an example of the I/O Function table included in the I/O bank report:

Figure 8-8 • I/O Function Table

This table lists the number of input I/Os, output I/Os, bidirectional I/Os, and differential input and output I/O pairs that use I/O and DDR registers.

Note: IGLOO nano and ProASIC3 nano devices do not support differential inputs.

Certain rules must be met to implement registered and DDR I/O functions (refer to the I/O Structures section of the handbook for the device you are using and the "DDR" section on page 190).

I/O Technology

The I/O Technology table (shown in Figure 8-9) gives the values of VCCI and VREF (reference voltage) for all the I/O standards used in the design. The user should assign these voltages appropriately.

Figure 8-9 • I/O Technology Table

those banks, the user does not need to assign the same VCCI voltage to another bank. The user needs to assign the other three VCCI voltages to three more banks.

Assigning Technologies and VREF to I/O Banks

Low power flash devices offer a wide variety of I/O standards, including voltage-referenced standards. Before proceeding to Layout, each bank must have the required VCCI voltage assigned for the corresponding I/O technologies used for that bank. The voltage-referenced standards require the use of a reference voltage (VREF). This assignment can be done manually or automatically. The following sections describe this in detail.

Manually Assigning Technologies to I/O Banks

The user can import the PDC at this point and resolve this requirement. The PDC command is

```
set_iobank [bank name] -vcci [vcci value]
```

Another method is to use the I/O Bank Settings dialog box (**MVN > Edit > I/O Bank Settings**) to set up the V_{CCI} voltage for the bank (Figure 8-12).

Figure 8-12 • Setting VCCI for a Bank

Input Support for DDR

The basic structure to support a DDR input is shown in Figure 9-2. Three input registers are used to capture incoming data, which is presented to the core on each rising edge of the I/O register clock. Each I/O tile supports DDR inputs.

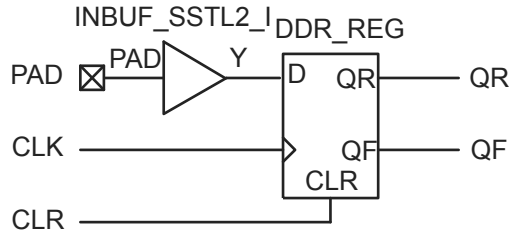


Figure 9-2 • DDR Input Register Support in Low Power Flash Devices

Output Support for DDR

The basic DDR output structure is shown in Figure 9-1 on page 205. New data is presented to the output every half clock cycle.

Note: DDR macros and I/O registers do not require additional routing. The combiner automatically recognizes the DDR macro and pushes its registers to the I/O register area at the edge of the chip. The routing delay from the I/O registers to the I/O buffers is already taken into account in the DDR macro.

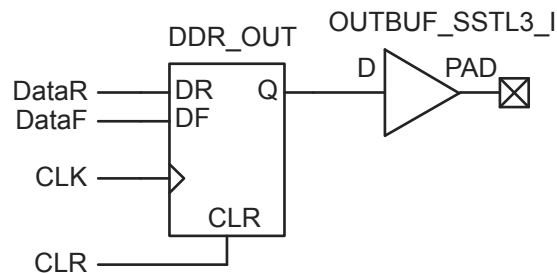


Figure 9-3 • DDR Output Register (SSTL3 Class I)

Signal Integrity While Using ISP

For ISP of flash devices, customers are expected to follow the board-level guidelines provided on the Microsemi SoC Products Group website. These guidelines are discussed in the datasheets and application notes (refer to the “Related Documents” section of the datasheet for application note links). Customers are also expected to troubleshoot board-level signal integrity issues by measuring voltages and taking oscilloscope plots.

Programming Failure Allowances

Microsemi has strict policies regarding programming failure allowances. Please refer to *Programming and Functional Failure Guidelines* on the Microsemi SoC Products Group website for details.

Contacting the Customer Support Group

Highly skilled engineers staff the Customer Applications Center from 7:00 A.M. to 6:00 P.M., Pacific time, Monday through Friday. You can contact the center by one of the following methods:

Electronic Mail

You can communicate your technical questions to our email address and receive answers back by email, fax, or phone. Also, if you have design problems, you can email your design files to receive assistance. Microsemi monitors the email account throughout the day. When sending your request to us, please be sure to include your full name, company name, and contact information for efficient processing of your request. The technical support email address is soc_tech@microsemi.com.

Telephone

Our Technical Support Hotline answers all calls. The center retrieves information, such as your name, company name, telephone number, and question. Once this is done, a case number is assigned. Then the center forwards the information to a queue where the first available applications engineer receives the data and returns your call. The phone hours are from 7:00 A.M. to 6:00 P.M., Pacific time, Monday through Friday.

The Customer Applications Center number is (800) 262-1060.

European customers can call +44 (0) 1256 305 600.

3. Choose the desired settings for the FlashROM configurations to be programmed (Figure 11-13). Click **Finish** to generate the STAPL programming file for the design.
-

Figure 11-13 • FlashROM Configuration Settings for Low Power Flash Devices

Generation of Security Header Programming File Only— Application 2

As mentioned in the "Application 2: Nontrusted Environment—Unsecured Location" section on page 243, the designer may employ FlashLock Pass Key protection or FlashLock Pass Key with AES encryption on the device before sending it to a nontrusted or unsecured location for device programming. To achieve this, the user needs to generate a programming file containing only the security settings desired (Security Header programming file).

Note: If AES encryption is configured, FlashLock Pass Key protection must also be configured.

The available security options are indicated in Table 11-4 and Table 11-5 on page 251.

Table 11-4 • FlashLock Security Options for IGLOO and ProASIC3

Security Option	FlashROM Only	FPGA Core Only	Both FlashROM and FPGA
No AES / no FlashLock	—	—	—
FlashLock only	✓	✓	✓
AES and FlashLock	✓	✓	✓

Programming Voltage (VPUMP) and VJTAG

Low-power flash devices support on-chip charge pumps, and therefore require only a single 3.3 V programming voltage for the VPUMP pin during programming. When the device is not being programmed, the VPUMP pin can be left floating or can be tied (pulled up) to any voltage between 0 V and 3.6 V². During programming, the target board or the FlashPro4/3/3X programmer can provide VPUMP. FlashPro4/3/3X is capable of supplying VPUMP to a single device. If more than one device is to be programmed using FlashPro4/3/3X on a given board, FlashPro4/3/3X should not be relied on to supply the VPUMP voltage. A FlashPro4/3/3X programmer is not capable of providing reliable VJTAG voltage. The board must supply VJTAG voltage to the device and the VJTAG pin of the programmer header must be connected to the device VJTAG pin. Microsemi recommends that VPUMP³ and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail. Refer to the "Board-Level Considerations" section on page 271 for capacitor requirements.

Low power flash device I/Os support a bank-based, voltage-supply architecture that simultaneously supports multiple I/O voltage standards (Table 12-2). By isolating the JTAG power supply in a separate bank from the user I/Os, low power flash devices provide greater flexibility with supply selection and simplify power supply and printed circuit board (PCB) design. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Microsemi recommends that TCK be tied to GND through a 200 ohm to 1 Kohm resistor. This prevents a possible totempole current on the input buffer stage. For TDI, TMS, and TRST pins, the devices provide an internal nominal 10 Kohm pull-up resistor. During programming, all I/O pins, except for JTAG interface pins, are tristated and weakly pulled up to VCCI. This isolates the part and prevents the signals from floating. The JTAG interface pins are driven by the FlashPro4/3/3X during programming, including the TRST pin, which is driven HIGH.

Table 12-2 • Power Supplies

Power Supply	Programming Mode	Current during Programming
VCC	1.2 V / 1.5 V	< 70 mA
VCCI	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V (bank-selectable)	I/Os are weakly pulled up.
VJTAG	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V	< 20 mA
VPUMP	3.15 V to 3.45 V	< 80 mA

Note: All supply voltages should be at 1.5 V or higher, regardless of the setting during normal operation, except for IGLOO nano, where 1.2 V VCC and VJTAG programming is allowed.

Nonvolatile Memory (NVM) Programming Voltage

SmartFusion and Fusion devices need stable VCCNVM/VCCENV³ (1.5 V power supply to the embedded nonvolatile memory blocks) and VCCOSC/VCCROSC⁴ (3.3 V power supply to the integrated RC oscillator). The tolerance of VCCNVM/VCCENV is $\pm 5\%$ and VCCOSC/VCCROSC is $\pm 5\%$.

Unstable supply voltage on these pins can cause an NVM programming failure due to NVM page corruption. The NVM page can also be corrupted if the NVM reset pin has noise. This signal must be tied off properly.

Microsemi recommends installing the following capacitors⁵ on the VCCNVM/VCCENV and VCCOSC/VCCROSC pins:

- Add one bypass capacitor of 10 μ F for each power supply plane followed by an array of decoupling capacitors of 0.1 μ F.
- Add one 0.1 μ F capacitor near each pin.

2. During sleep mode in IGLOO devices connect VPUMP to GND.
3. VPUMP has to be quiet for successful programming. Therefore VPUMP must be separate and required capacitors must be installed close to the FPGA VPUMP pin.
4. VCCROSC is for SmartFusion.
5. The capacitors cannot guarantee reliable operation of the device if the board layout is not done properly.

3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.

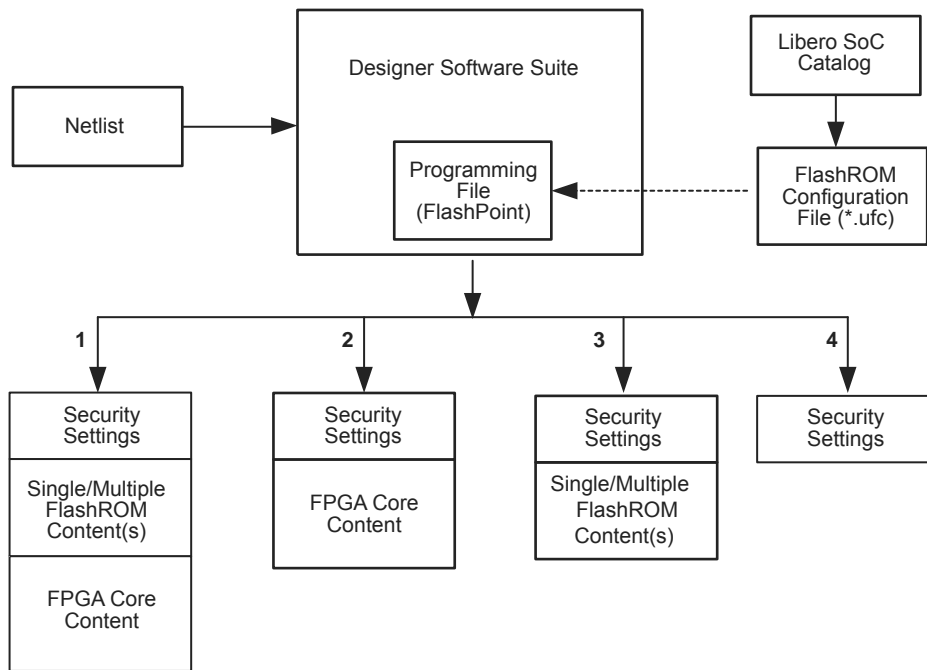


Figure 12-4 • Flexible Programming File Generation for Different Applications

Programming Solution

For device programming, any IEEE 1532-compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock – TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file – STAPL
- Daisy chain – Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming – Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply – The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

Circuit Verification

The power switching circuit recommended above is implemented on Microsemi's Icicle board (Figure 13-2). On the Icicle board, VJTAGENB is used to control the N-Channel Digital FET; however, this circuit was modified to use TRST instead of VJTAGENB in this application. There are three important aspects of this circuit that were verified:

1. The rise on VCC from 1.2 V to 1.5 V when TRST is HIGH
2. VCC rises to 1.5 V before programming begins.
3. VCC switches from 1.5 V to 1.2 V when TRST is LOW.

Verification Steps

1. The rise on VCC from 1.2 V to 1.5 V when TRST is HIGH.
-

Figure 13-2 • Core Voltage on the IGLOO AGL125-QNG132 Device

In the oscilloscope plots (Figure 13-2), the TRST from FlashPro3 and the VCC core voltage of the IGLOO device are labeled. This plot shows the rise characteristic of the TRST signal from FlashPro3. Once the TRST signal is asserted HIGH, the LTC3025 shown in Figure 13-1 on page 277 senses the increase in voltage and changes the output from 1.2 V to 1.5 V. It takes the circuit approximately 100 μ s to respond to TRST and change the voltage to 1.5 V on the VCC core.

STAPL vs. DirectC

Programming the low power flash devices is performed using DirectC or the STAPL player. Both tools use the STAPL file as an input. DirectC is a compiled language, whereas STAPL is an interpreted language. Microprocessors will be able to load the FPGA using DirectC much more quickly than STAPL. This speed advantage becomes more apparent when lower clock speeds of 8- or 16-bit microprocessors are used. DirectC also requires less memory than STAPL, since the programming algorithm is directly implemented. STAPL does have one advantage over DirectC—the ability to upgrade. When a new programming algorithm is required, the STAPL user simply needs to regenerate a STAPL file using the latest version of the Designer software and download it to the system. The DirectC user must download the latest version of DirectC from Microsemi, compile everything, and download the result into the system (Figure 14-4).

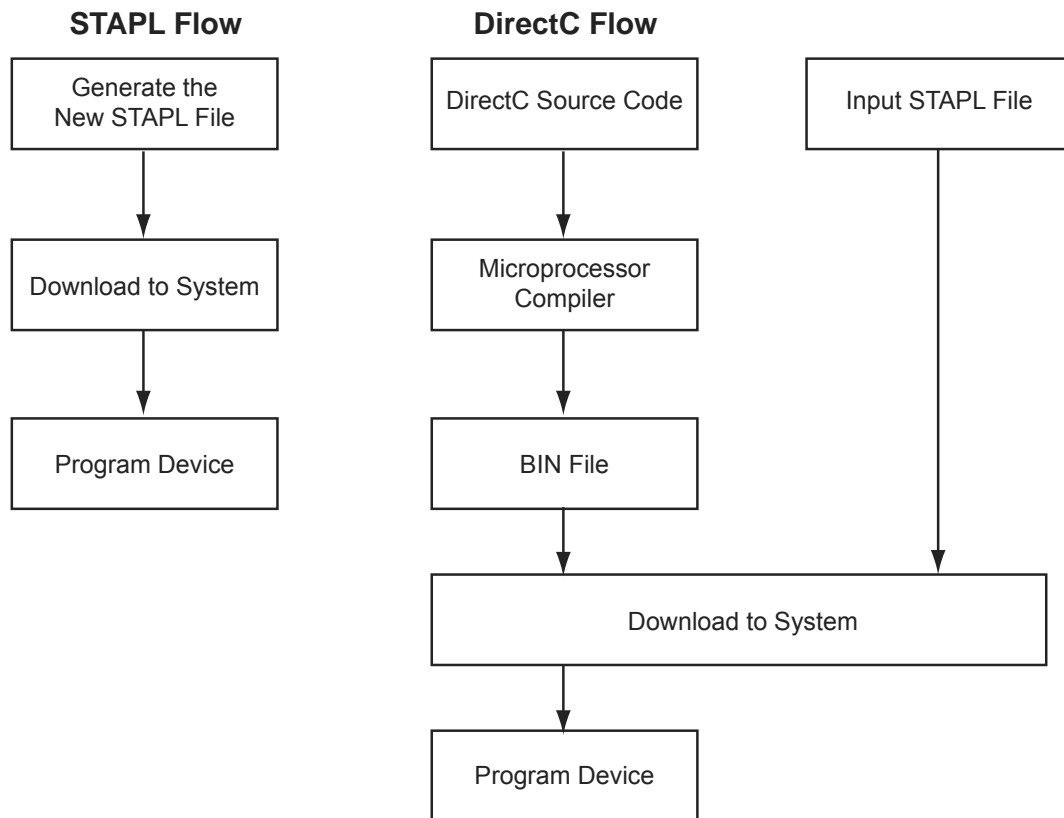


Figure 14-4 • STAPL vs. DirectC

Microsemi's Flash Devices Support the JTAG Feature

The flash-based FPGAs listed in Table 15-1 support the JTAG feature and the functions described in this document.

Table 15-1 • Flash-Based FPGAs

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC®3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 15-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 15-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.